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### Abstract

The pellicle is necessary to prevent defect printing and to increase the yield in extreme ultra-violet lithography (EUVL). The thickness of the pellicle should be nanometer thin and the deflection due to gravity was thought to be very large. Although the mesh support reduces the deflection, it could cause serious non-uniform intensity distribution and local critical dimension uniformity variation. Therefore, if possible, the free-standing pellicle is preferred. We revisited the possible large deflection of the thin membrane, and found that the non-linear deflection term was added to the deflection if the deflection was large compared to the thickness of plate. It turned out that the deflection of the thin free-standing full scale pellicle was less than the desired specification. Our result shows that a mesh grid support to prevent the deflection is not necessary for the EUV pellicle.



deflection would be large.

## Deflection of the full scale free standing EUV pellicle is OK Eun-Sang Park\*, Zahid Hussain Shamsi, Ji-Won Kim, Dai-Gyoung Kim, and Hye-Keun Oh

structure causes the CD variation.

## **Nonlinear deflection**



# Conclusion

- $\checkmark$  The linear analysis shows the deflection of the silicon pellicle was very large,  $\sim 1000$  m @ 50 nm thickness.

- ✓ Therefore, a mesh grid support to prevent the deflection is not necessary for the EUV pellicle.



✓ The non-linear deflection term is added to the deflection since the deflection at the center is very large compared to the thickness of plate.  $\checkmark$  The deflection of the full reticle scale free-standing pellicle is very small,  $\sim 100 \,\mu m @ 50 \,nm$ , with non-linear deflection.

